



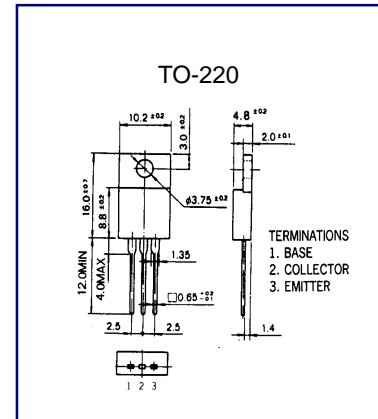
2SB825

PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CE0}	-60	V
Emitter-Base voltage	V _{EB0}	-5	V
Collector Current (DC)	I _C	-7	A
Collector Dissipation (T _c =25°C)	P _C	40	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C



ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = -50V , I _E =0			-10	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = -5V , I _C =0			10	μA
DC Current Gain	h _{FE1}	V _{CE} = -2V , I _C =-1.0A	100			
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =-4A , I _B =-0.4A			-0.4	V
Current Gain Bandwidth Product	f _T	V _{CE} = -2V , I _C =-0.5A		8		MHZ